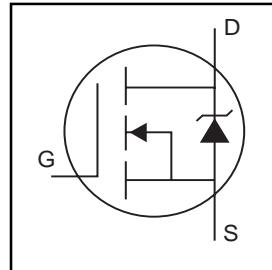


# IRF3205S/L

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



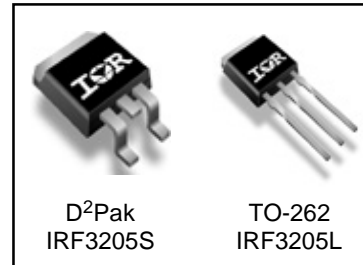
$V_{DSS} = 55V$
$R_{DS(on)} = 8.0m\Omega$
$I_D = 110A^{\text{⑤}}$

## Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF3205L) is available for low-profile applications.



D<sup>2</sup>Pak  
IRF3205S

TO-262  
IRF3205L

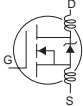
## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	110 <sup>⑤</sup>	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	80	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	390	
$P_D @ T_C = 25^\circ C$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_{AR}$	Avalanche Current <sup>①</sup>	62	A
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	20	mJ
dv/dt	Peak Diode Recovery dv/dt <sup>③</sup>	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 srew	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mounted, steady-state)*	—	40	

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	8.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 62A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	44	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 62A④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	146	nC	I <sub>D</sub> = 62A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	35		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	54		V <sub>GS</sub> = 10V, See Fig. 6 and 13
t <sub>d(on)</sub>	Turn-On Delay Time	—	14	—	ns	V <sub>DD</sub> = 28V
t <sub>r</sub>	Rise Time	—	101	—		I <sub>D</sub> = 62A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	50	—		R <sub>G</sub> = 4.5Ω
t <sub>f</sub>	Fall Time	—	65	—		V <sub>GS</sub> = 10V, See Fig. 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	3247	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	781	—		V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	211	—		f = 1.0MHz, See Fig. 5
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	1050⑥	264⑦		mJ

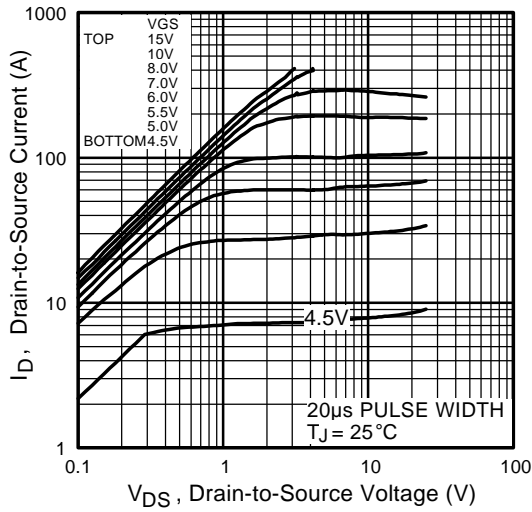
## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode)①	—	—	390		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 62A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	69	104	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 62A
Q <sub>rr</sub>	Reverse Recovery Charge	—	143	215	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

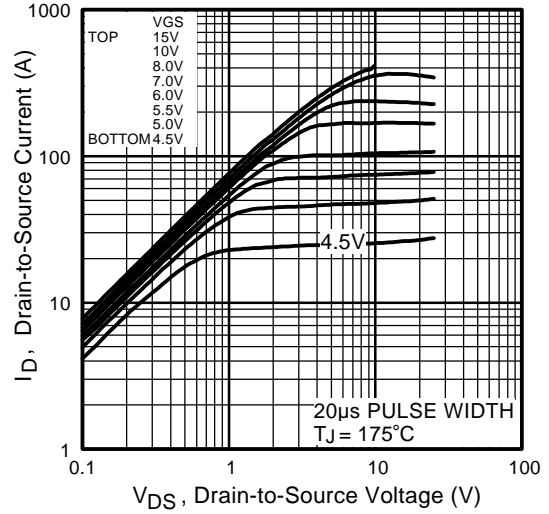
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting T<sub>J</sub> = 25°C, L = 138μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 62A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 62A, di/dt ≤ 207A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑥ This is a typical value at device destruction and represents operation outside rated limits.
- ⑦ This is a calculated value limited to T<sub>J</sub> = 175°C.

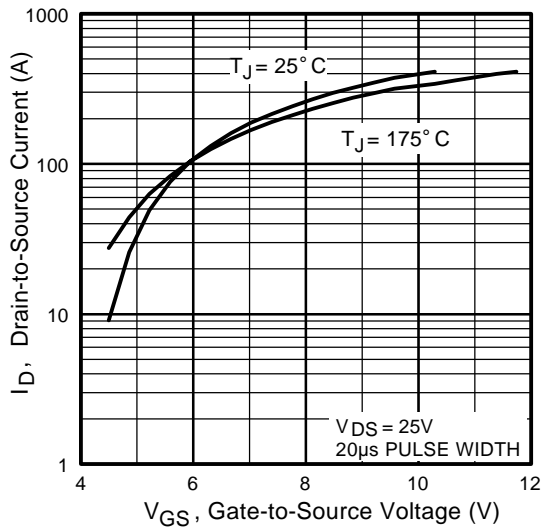
\* When mounted on 1" square PCB ( FR-4 or G-10 Material ).  
For recommended footprint and soldering techniques refer to application note #AN-994.



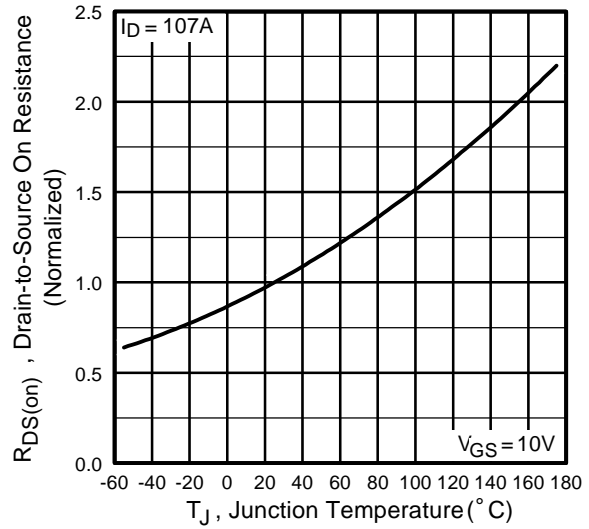
**Fig 1.** Typical Output Characteristics



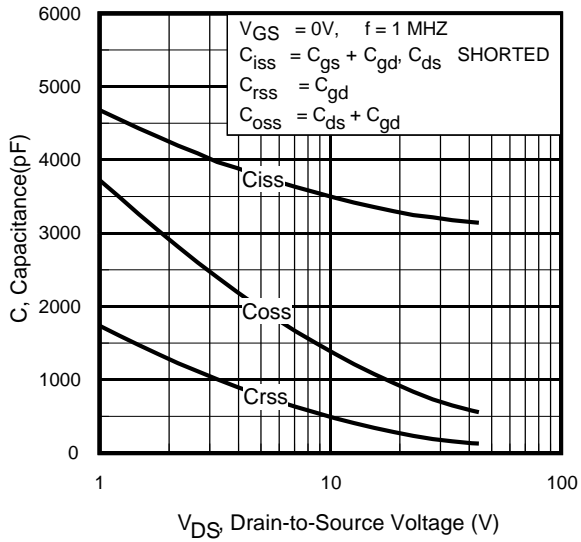
**Fig 2.** Typical Output Characteristics



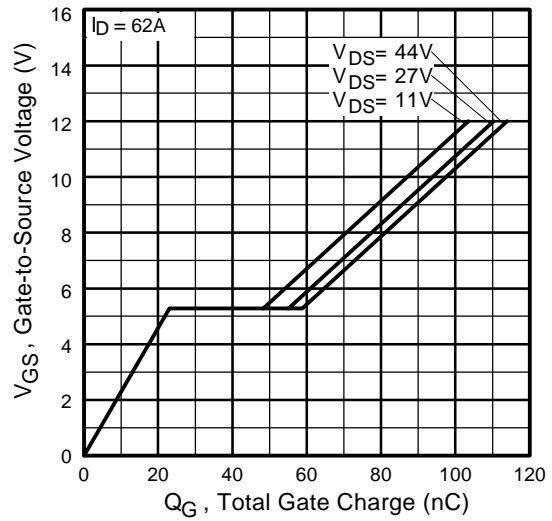
**Fig 3.** Typical Transfer Characteristics



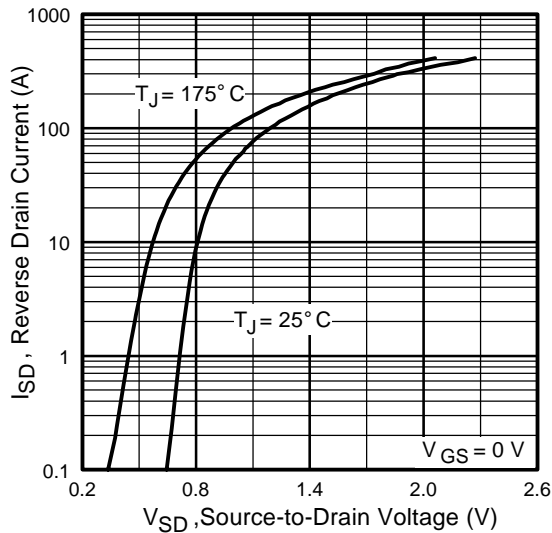
**Fig 4.** Normalized On-Resistance Vs. Temperature



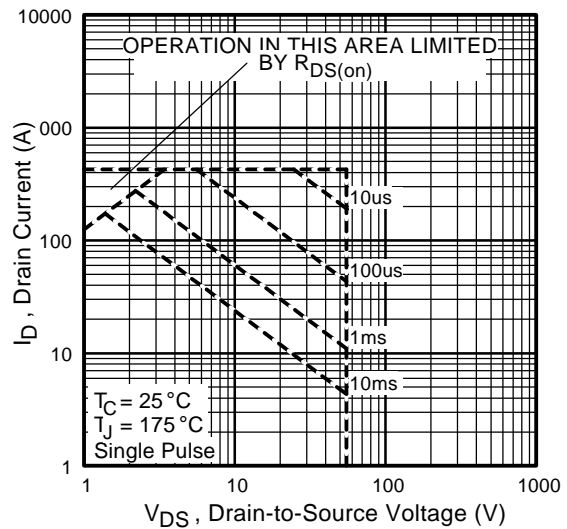
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

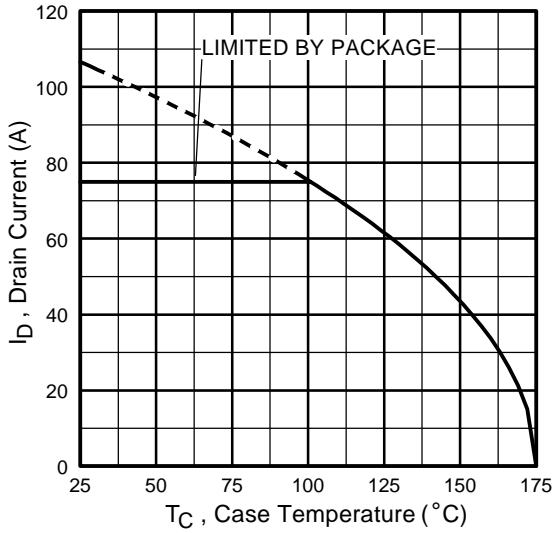


Fig 9. Maximum Drain Current Vs. Case Temperature

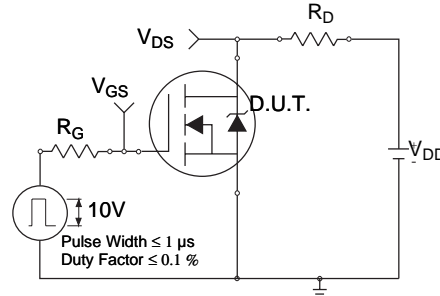


Fig 10a. Switching Time Test Circuit

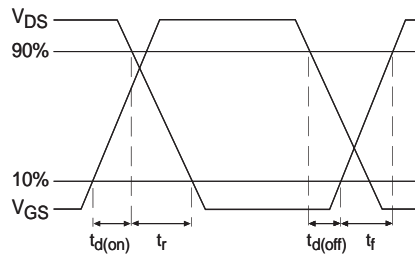


Fig 10b. Switching Time Waveforms

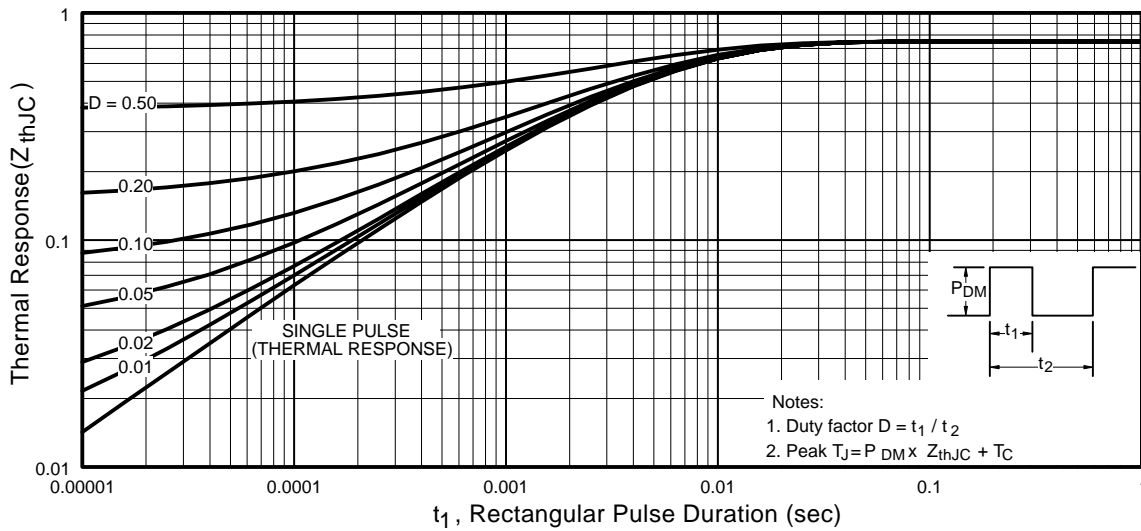
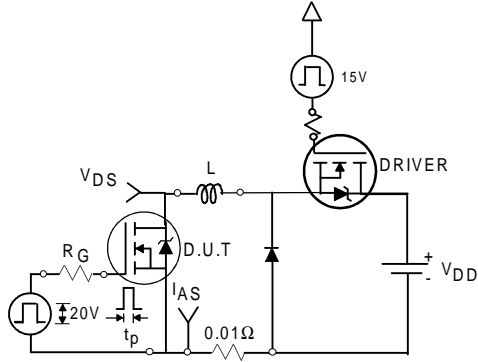


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRF3205S/L



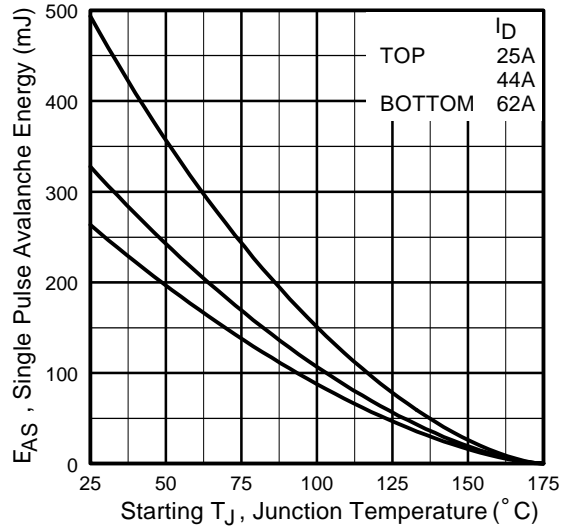
**Fig 12a.** Unclamped Inductive Test Circuit



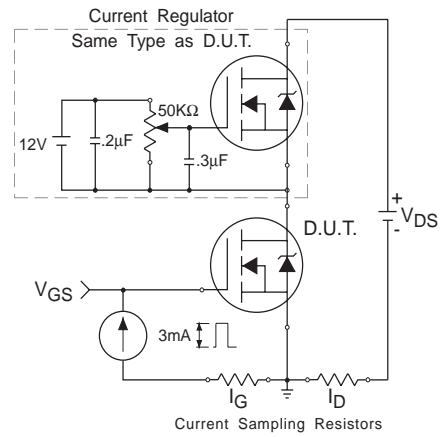
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

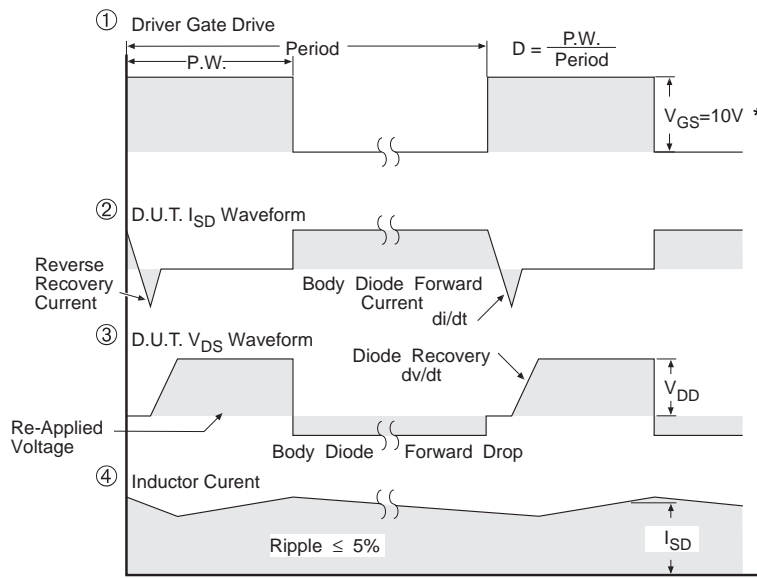
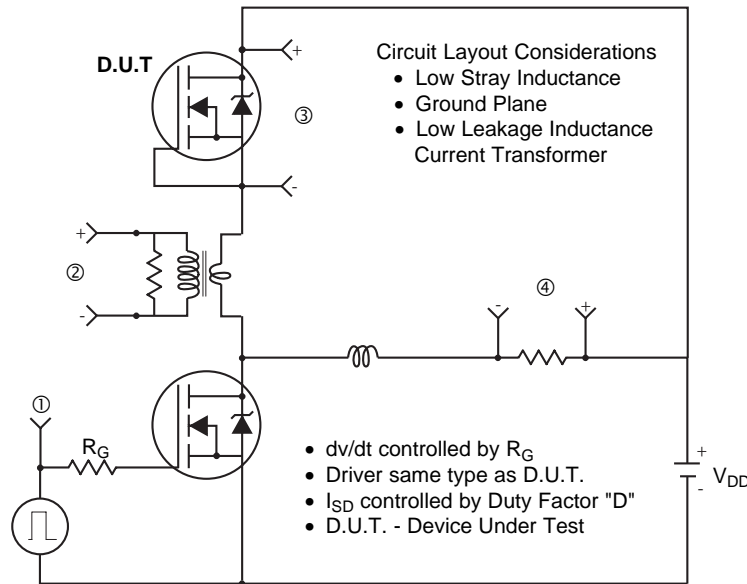


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



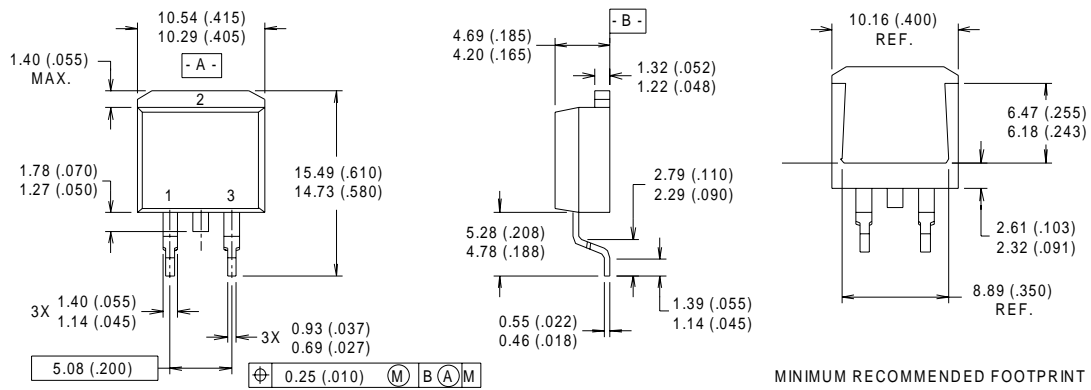
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFETS

# IRF3205S/L



## D<sup>2</sup>Pak Package Outline



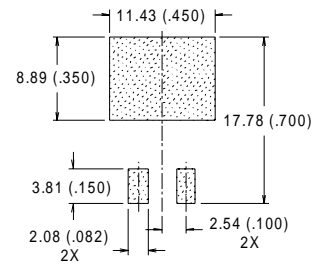
### NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

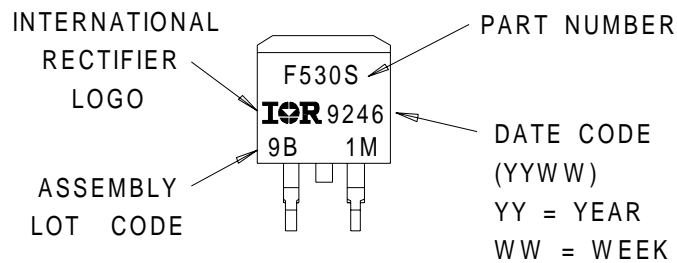
### LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

### MINIMUM RECOMMENDED FOOTPRINT

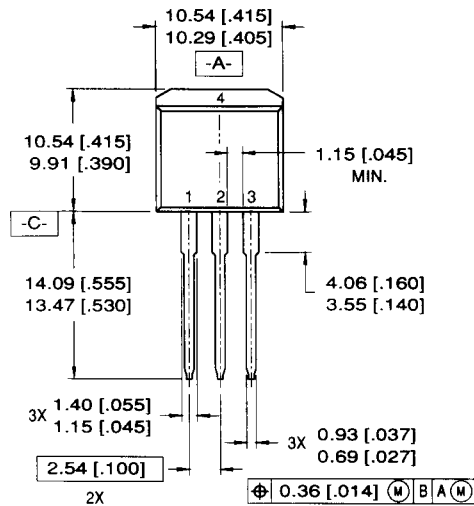


## D<sup>2</sup>Pak Part Marking Information



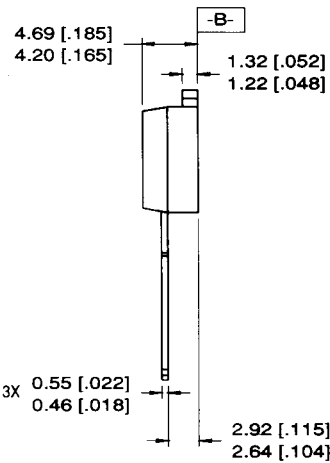


## TO-262 Package Outline



**LEAD ASSIGNMENTS**

- |           |            |
|-----------|------------|
| 1 = GATE  | 3 = SOURCE |
| 2 = DRAIN | 4 = DRAIN  |

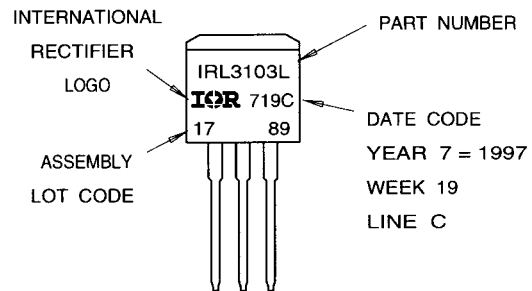


**NOTES:**

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

## TO-262 Part Marking Information

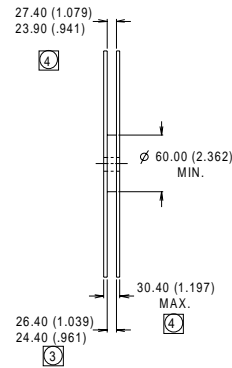
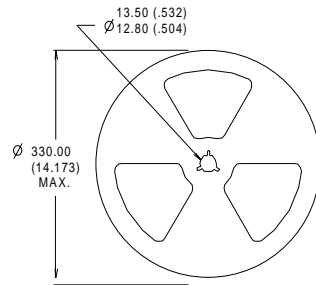
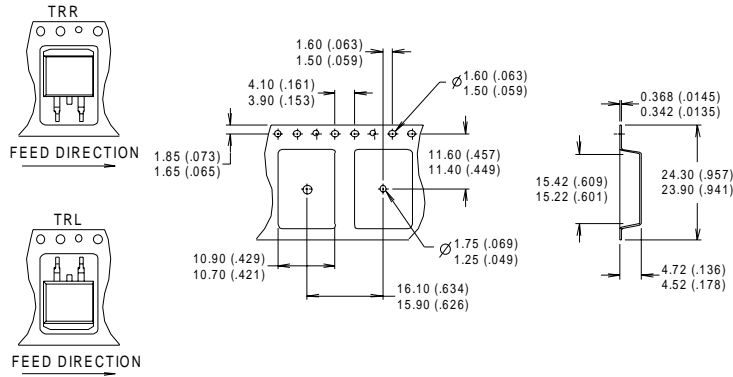
EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



# IRF3205S/L



## D<sup>2</sup>Pak Tape & Reel Information



- NOTES:
1. CONFORMS TO EIA-418.
  2. CONTROLLING DIMENSION: MILLIMETER.
  - ③ DIMENSION MEASURED @ HUB.
  - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the industrial market.  
 Qualification Standards can be found on IR's Web site.



**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
 TAC Fax: (310) 252-7903

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